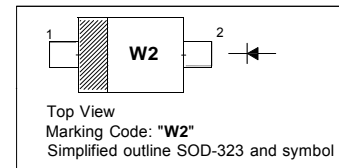


Silicon Epitaxial Planar Switching Diode

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

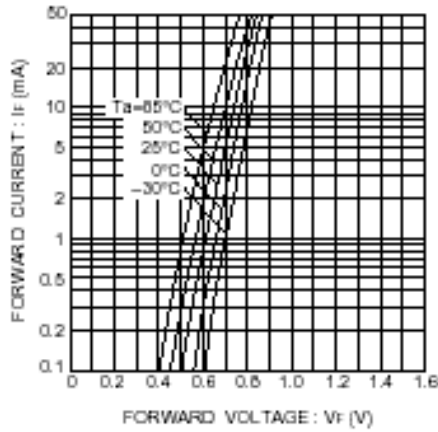


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

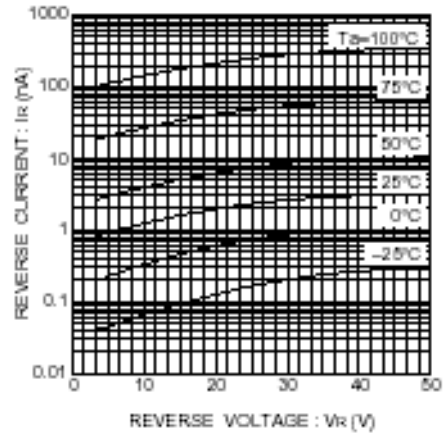
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	85	V
Reverse Voltage	V_R	75	V
Continuous Forward Current	I_F	125	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$	0.5
		at $t = 1\text{ ms}$	1
		at $t = 1\text{ }\mu\text{s}$	4
Power Dissipation	P_{tot}	250	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

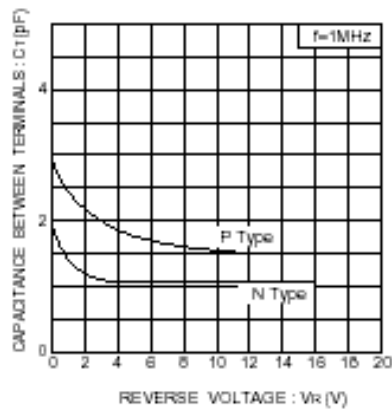
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	715	mV
		855	mV
		1	V
		1.25	V
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	I_R	30	nA
		1	μA
		30	μA
		50	μA
Diode Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_d	2	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$, $I_R = 10\text{ mA}$, $R_L = 100\text{ }\Omega$	t_{rr}	4	ns



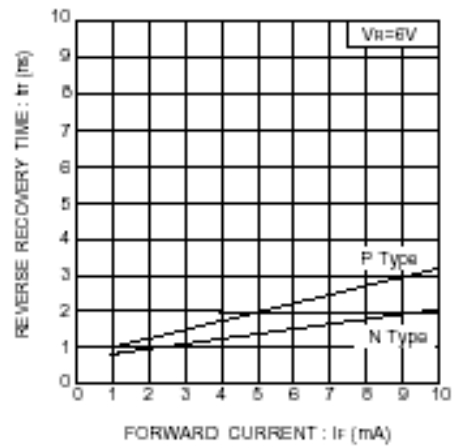
Forward characteristics



Reverse characteristics



Capacitance between terminals characteristics

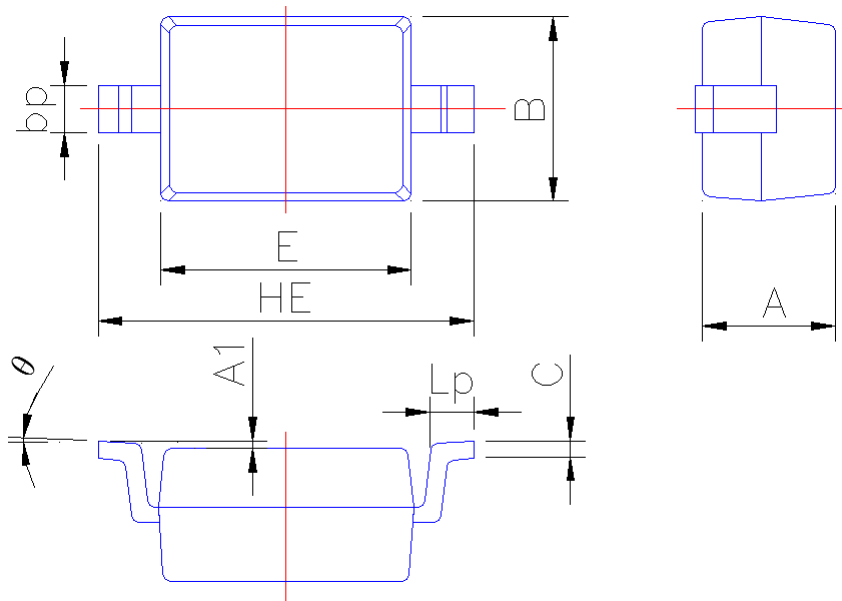


Reverse recovery time

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°